



PRODUCT SPECIFICATION

Model No : CSD-822B7/823B7

Descriptions:

- 0.8 Inch Dual Digits Display
- CSD-822: Common Anode
- CSD-823: Common Cathode
- Emitting Color: Super Bright Blue



CUSTOMER APPROVED SIGNATURES	APPROVED BY	CHECKED BY	PREPARED BY

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Model No : CSD-822/823B7

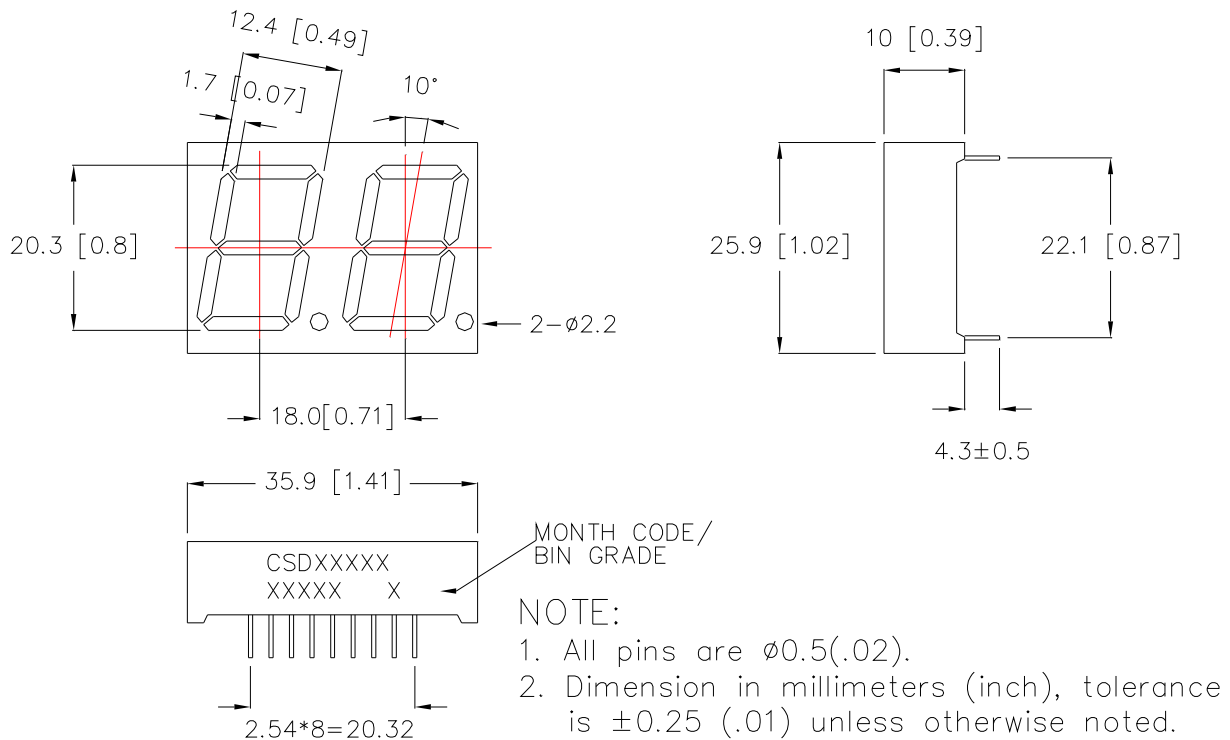
Features -

1. 0.8 inch (20.3mm) digit height.
2. Case mold type.
3. RoHs compliant.
4. Low power consumption.
5. Easy mounting on P.C. board or socket.

Device Selection Guide -

Part No.	Chip		Description
	Material	Emitted Color	
CSD-822B7	InGaN	Super Bright Blue	Common Anode
CSD-823B7	InGaN	Super Bright Blue	Common Cathode

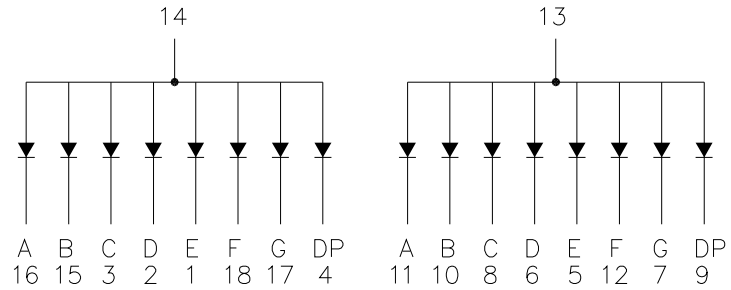
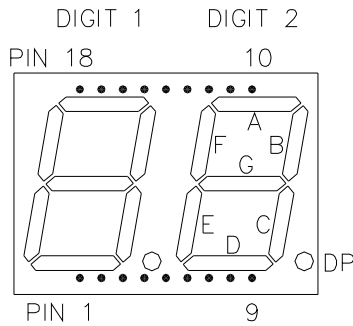
Package Dimensions -





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Internal Circuit Diagrams -



CSS-822 Common Anode.
(CSS-823 is Common Cathode.)

Absolute Maximum Rating -

(Ta=25°C)

Parameter	Symbol	Rating	Unit
Power Dissipation Per Dice	Pd	120	mW
Continuous Forward Current Per Dice	IAF	30	mA
Peak Current Per Dice(Duty cycle 1/10,1KHz)	IPF	100	mA
Derating Linear From 25°C Per Dice	-	0.4	mA/°C
Reverse Voltage Per Dice	VR	5	V
Operating Temp.	Topr	-35 ~ +85	°C
Storage Temp.	Tstg	-35 ~ +85	°C
Solder temperature 1/16 inch below seating plane for 3 seconds at 260°C			



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■ Electro-optical Characteristics -

(Ta=25°C)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Condition
Forward Voltage Per Segment	V _F	-	3.2	4	V	I _F =20mA
Luminous Intensity Per Segment	I _v	-	20	-	mcd	I _F =10mA
Dominant Wavelength	λ _d	-	470	-	nm	I _F =20mA
Spectrum Radiation Bandwidth	Δλ	-	20	-	nm	I _F =20mA
Reverse Current	I _R	-	-	100	μA	V _R =5V
Luminous Intensity Matching Ratio	I _{V-m}	-	-	2:1	-	I _F =10mA



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Typical Electrical / Optical Charateristics Curves -

(Ta = 25°C Unless Otherwise Noted)

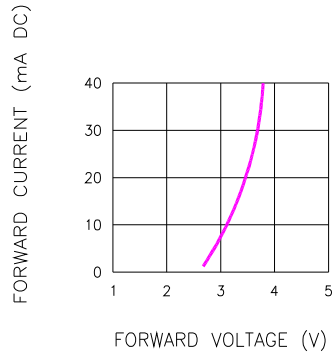


Fig.1 FORWARD CURRENT VS. FORWARD VOLTAGE

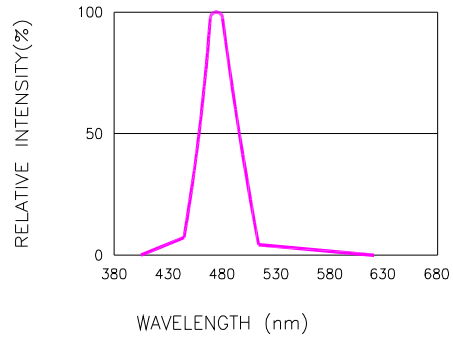


Fig.2 RELATIVE INTENSITY VS. WAVELENGTH

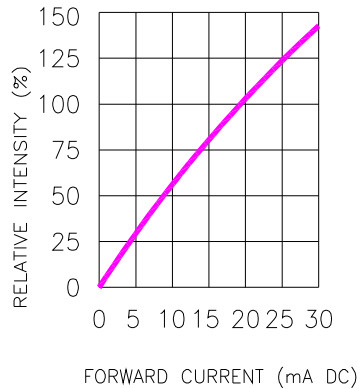


Fig.3 RELATIVE INTENSITY VS. FORWARD CURRENT

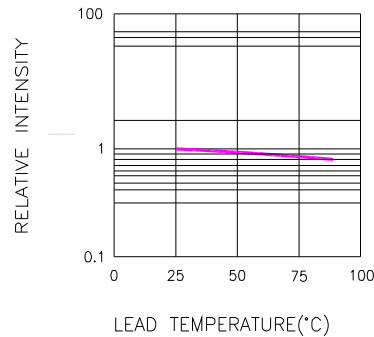


Fig.4 RELATIVE INTENSITY VS. LEAD TEMPERATURE
(PULSED 20 mA; 300us
PULSE, 10ms PERIOD)

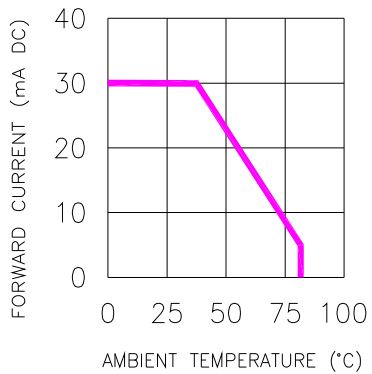


Fig.5 FORWARD CURRENT VS. AMBIENT TEMPERATURE

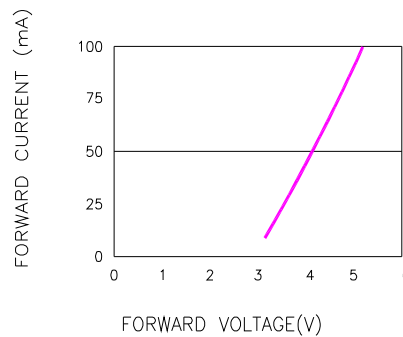


Fig.6 PEAK FORWARD VOLTAGE VS. FORWARD (100us TEST PULSE, 1% DUTY CYCLE)